

## T541X107M020AH6510

Aliases (DLA Drawing 04052-058)

T541 HRA, Tantalum, Polymer Tantalum, HRA Multi-Anode, 100 uF, 20%, 20 VDC, SMD, Polymer, Molded, High Reliability, Multi-Anode, Low ESR, N/A, 50 mOhms, 7343, 4.3mm

CATHODE (-) END VIEW

Termination cutout at KEMET's option, either end

ANODE (+) END VIEW

BOTTOM VIEW

SIDE VIEW



General Information	
Series	T541 HRA
Dielectric	Polymer Tantalum
Style	SMD Chip
Description	SMD, Polymer, Molded, High Reliability, Multi-Anode, Low ESR
Features	Non-Combustible, Multiple Anode, Low ESR, High Reliability
RoHS	No
Prop 65	WARNING: Cancer and reproductive harm - https://www.p65warnings.ca.gov /
SCIP Number	b064b03e-bd75-42af-b342-1fe 94dec2340
Termination	Tin Lead (SnPb)
Qualifications	DLA Drawing 04052
AEC-Q200	No
Typical Component Weight	410.89 mg
Shelf Life	52 Weeks
MSL	3

Dimensions	
Footprint	7343
L	7.3mm +/-0.3mm
W	4.3mm +/-0.3mm
н	4mm +/-0.3mm
т	0.13mm REF
S	1.3mm +/-0.3mm
F	2.4mm +/-0.1mm
А	3.8mm MIN
В	0.5mm +/-0.15mm
E	3.5mm REF
G	3.5mm REF
Р	1.7mm REF
R	1mm REF
Х	0.1mm +/-0.1mm REF

Specifications	
Capacitance	100 uF
Capacitance Tolerance	20%
Voltage DC	20 VDC (105C), 13.4 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	105°C
Life	2000 Hrs (125C)
Humidity	60C, 90% RH, 500 Hours, rated voltage
Dissipation Factor	10% 120Hz 25C
Failure Rate	N/A
ESR	50 mOhms (100kHz 25C)
Ripple Current	2324 mA (rms, 100kHz 45C)
Leakage Current	200 uA (5min 25°C)
Testing and Reliability	4 Cycles At +25C +/-5C Before Voltage Aging

# Packaging Specifications Packaging T&R, 178mm Packaging Quantity 500

Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

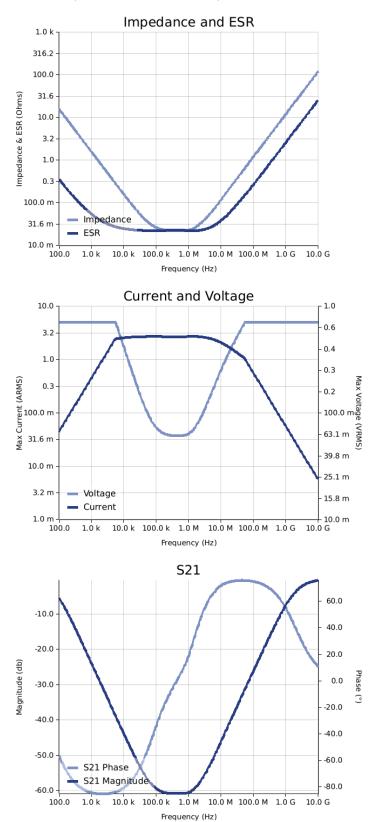


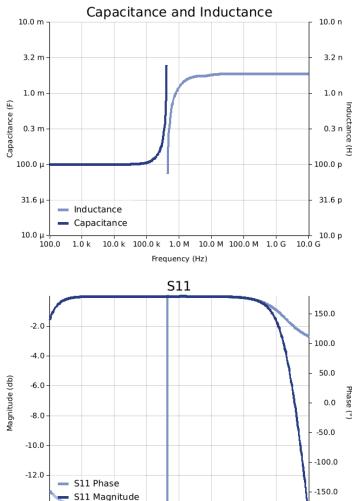
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### Simulations

For the complete simulation environment please visit K-SIM.





-14.0

100.0

1.0 k

10.0 k 100.0 k 1.0 M

Frequency (Hz)

10.0 M 100.0 M 1.0 G

10.0 G



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#### These are simulations. This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.

- The ESR used for hipple klipple current/ voltage vs. requericy plots is the ESR at an originatine.
  The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
  The effects shown herein are based on measured data from a multiple part sample of the parts in question.
  Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
  The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages are applied to reach previous the barrent of the mean statement of the mean statement of the mean statement of the mean statement of the statement of the statement of the mean statement of the statement of the
- generated at any other harmonics. Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.